	Hits	Search Text	DBs
1	14708	(integrated cluster multi$1chamber) and ((wet rinse) same (dry plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	4098	((integrated cluster multi$1chamber) and ((wet rinse) same (dry plasma))) and (wet near dry)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	18	((integrated cluster multi$1chamber) and ((wet rinse) same (dry plasma))) and (((wet rins$3) near chamber) same ((dry plasma) near chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	4	((integrated cluster multi$1chamber) and ((wet rinse) same (dry plasma))) and ((rins$3 adj chamber) same ((dry etch$3 plasma) adj chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	0	APM with "9600"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	2	APM same "9600"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	1	("5127987").PN.	USPAT
8	1	("5007981").PN.	USPAT
9	186	wet with dry with process$3 with chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	11	(wet with dry with process$3 with chamber) and (wet adj dry with process$3 adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	15	(wet with dry with process$3 with chamber) and (wet near dry with process$3 near chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	4	((wet with dry with process$3 with chamber) and (wet near dry with process$3 near chamber)) not ((wet with dry with process$3 with chamber) and (wet adj dry with process$3 adj chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	140	(wet with dry with process$3 with chamber) and ("200" adj ".degree." c)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	0	(wet with dry with process$3 with chamber) and ("200" adj ".degree." adj c)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	1	(wet with dry with process$3 with chamber) and ("200" near c)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	0	(wet with dry with process$3 with chamber) and ("175" near c)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
17	3	(wet with dry with process$3 with chamber) and (("210" "215" "220" "225" "230" "235" "240" "245" "250" "255" "260" "265" "270" "275" "280" "285" "290" "295" "300") near c)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	34	(wet with dry with process$3 with chamber) and ((temperature heat$3) near (substrate wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	0	(wet with dry with process$3 with chamber) and (down adj stream near plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	5	(wet with dry with process$3 with chamber) and remote$2 near plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	2	(wet with dry with process$3 with chamber) and remote$2 with plasma not ((wet with dry with process$3 with chamber) and remote$2 near plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB